

## G2N5401

### PNP EPITAXIAL PLANAR TRANSISTOR

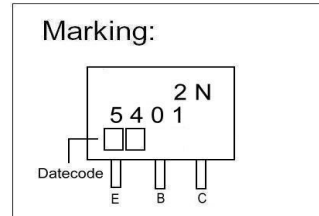
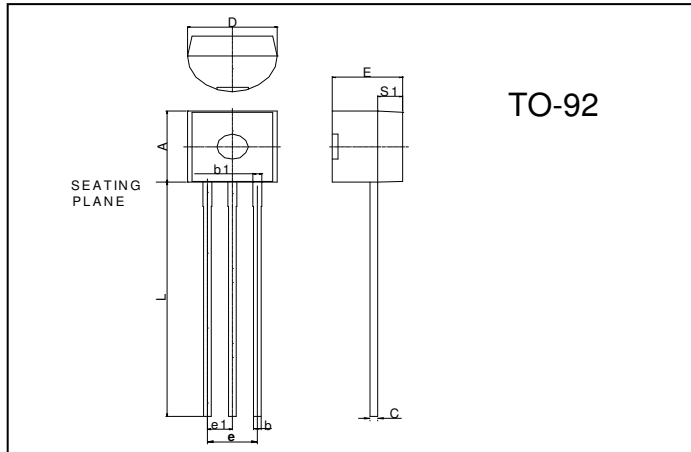
### Description

The G2N5401 is designed for general purpose applications requiring high breakdown voltages.

### Features

- \*Complementary to NPN Type G2N5551
- \*High Collector-Emitter Breakdown Voltage ( $V_{CE0}=150V@I_C=1mA$ )

### Package Dimensions



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	4.45	4.7	D	4.44	4.7
S1	1.02	-	E	3.30	3.81
b	0.36	0.51	L	12.70	-
b1	0.36	0.76	e1	1.150	1.390
C	0.36	0.51	e	2.42	2.66

### Absolute Maximum Ratings at $T_a = 25^\circ C$

Parameter	Symbol	Ratings	Unit
Junction Temperature	$T_j$	+150	$^\circ C$
Storage Temperature	$T_{stg}$	-55 ~ +150	$^\circ C$
Collector to Base Voltage	$V_{CBO}$	-160	V
Collector to Emitter Voltage	$V_{CEO}$	-150	V
Emitter to Base Voltage	$V_{EBO}$	-5	V
Collector Current	$I_C$	-600	mA
Total Power Dissipation	$P_D$	625	mW

### Characteristics at $T_a = 25^\circ C$

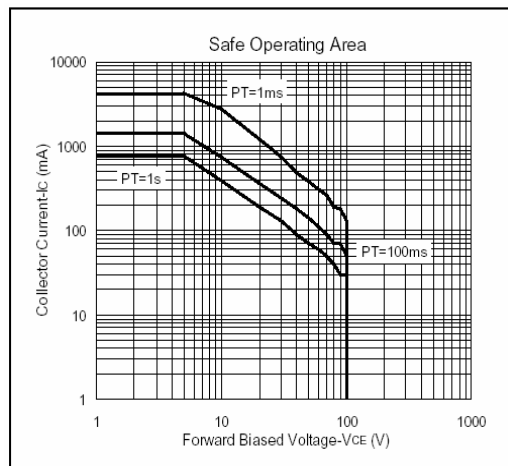
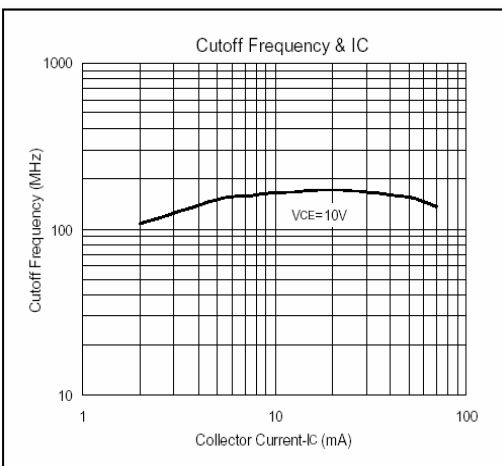
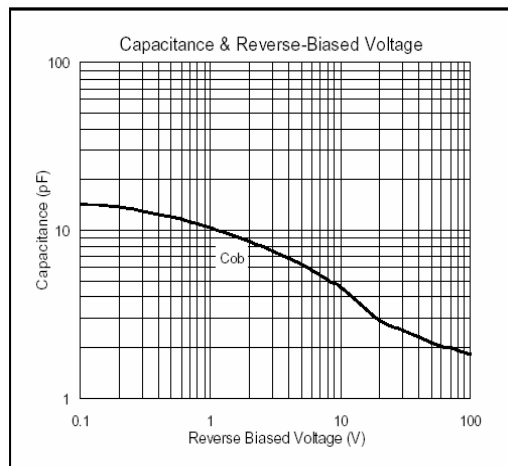
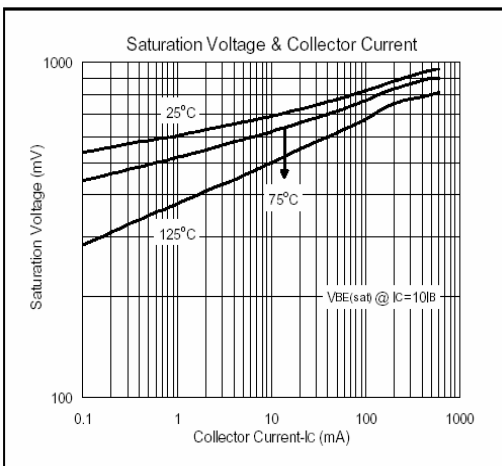
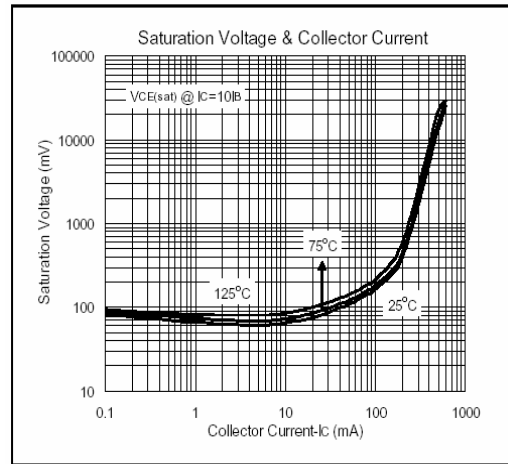
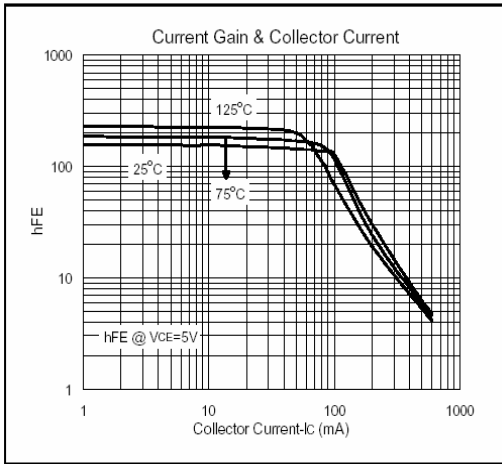
Symbol	Min.	Typ.	Max.	Unit	Test Conditions
$V_{CBO}$	-160	-	-	V	$I_C=-100\mu A, I_E=0$
$V_{CEO}$	-150	-	-	V	$I_C=-1mA, I_B=0$
$V_{EBO}$	-5	-	-	V	$I_E=-10\mu A, I_C=0$
$I_{CBO}$	-	-	-50	nA	$V_{CB}=-120V, I_E=0$
$I_{EBO}$	-	-	-50	nA	$V_{EB}=-3V, I_C=0$
* $V_{CE(sat)1}$	-	-	-0.2	V	$I_C=-10mA, I_B=-1mA$
* $V_{CE(sat)2}$	-	-	-0.5	mV	$I_C=-50mA, I_B=-5mA$
* $V_{BE(sat)1}$	-	-	-1	V	$I_C=-10mA, I_B=-1mA$
* $V_{BE(sat)2}$	-	-	-1	V	$I_C=-50mA, I_B=-5mA$
* $h_{FE1}$	50	-	-		$V_{CE}=-5V, I_B=-1mA$
* $h_{FE2}$	80	160	400		$V_{CE}=-5V, I_C=-10mA$
* $h_{FE3}$	50	-	-		$V_{CE}=-5V, I_C=-50mA$
$f_T$	100	-	300	MHz	$V_{CE}=-10V, I_C=-10mA, f=100MHz$
$C_{ob}$	-	-	6	pF	$V_{CB}=-10V, f=1MHz, I_E=0$

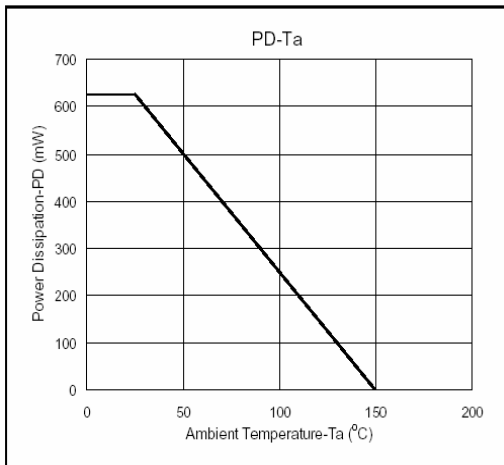
\* Pulse Test: Pulse Width  $\leq 380\mu s$ , Duty Cycle  $\leq 2\%$

### Classification Of $h_{FE2}$

Rank	A	N	C
Range	80-200	100-240	160-400

## Characteristics Curve





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